



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SURFACE MOUNT
SCHOTTKY DIODE**

VOLTAGE 40 Volts CURRENT 30 mAmperes

CH751WPT

APPLICATION

- * Ultra high speed switching

FEATURE

- * Small surface mounting type. (SC-70/SOT-323)
- * High speed. ($T_{RR}=2.0\text{nSec}$ Typ.)
- * Suitable for high packing density.
- * Maximum total power dissipation is 200mW.
- * Low forward voltage drop.

CONSTRUCTION

- * Silicon epitaxial planar

WEIGHT

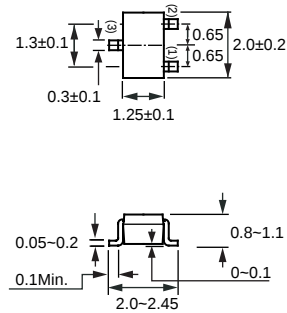
- * 0.006 grams (Approx.)

MARKING

- * MI



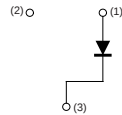
SC-70/SOT-323



Dimensions in millimeters

SC-70/SOT-323

CIRCUIT



RATINGS	SYMBOL	CH751WPT	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	Volts
Maximum RMS Voltage	V_{RMS}	28	Volts
Maximum DC Blocking Voltage	V_{DC}	40	Volts
Maximum Average Forward Rectified Current	I_O	30	mAmps
Peak Forward Surge Current at 8.3 mSec.	I_{FSM}	200	mAmps
Typical Junction Capacitance between Terminal (Note 1)	C_J	2.0	pF
Maximum Reverse Recovery Time (Note 2)	T_{RR}	2.0	nSec
Maximum Operating Temperature Range	T_J	-40 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-40 to +125	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (At $T_A = 25^{\circ}\text{C}$ unless otherwise noted)

CHARACTERISTICS	SYMBOL	CH751WPT			UNITS
		MIN.	TYP.	MAX.	
Maximum Instantaneous Forward Voltage at $I_F=1.0\text{mA}$	V_F	-	295	370	mVolts
Maximum Average Reverse Current at $V_R=10\text{V}$	I_R	-	150	1000	nAmps

- NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 1.0 volts.
2. Measured at applied forward current of 10mA and reverse current of 10mA.
3. ESD sensitive product handling required.

2002-10

RATING CHARACTERISTIC CURVES (CH751WPT)

FIG. 1 - FORWARD CHARACTERISTICS

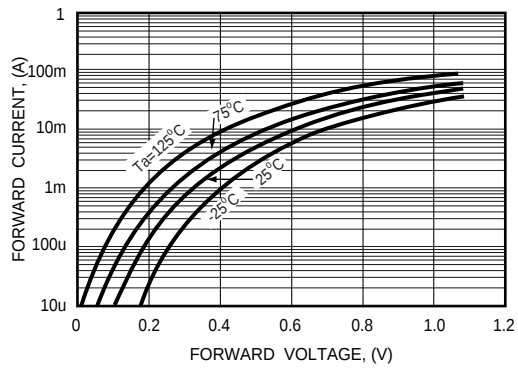


FIG. 2 - REVERSE CHARACTERISTICS

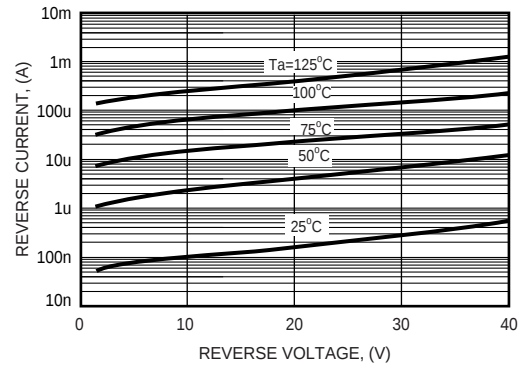


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

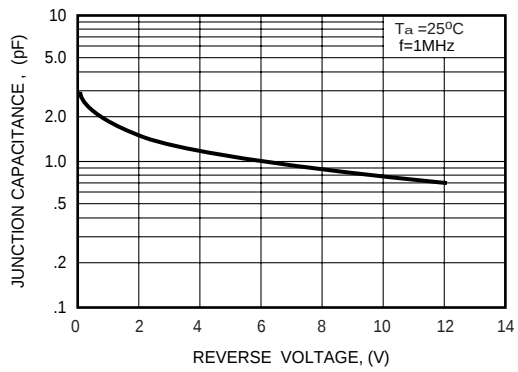


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

